

1SS390

SILICON EPITAXIAL PLANAR DIODE

Band Switching Diode

Features

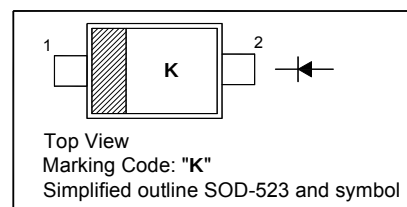
- Extremely small surface mounting type
- High reliability

Applications

- High frequency switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

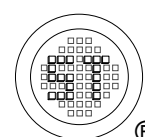


Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	35	V
Forward Current	I_F	100	mA
Junction Temperature	T_J	125	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	1	V
Reverse Current at $V_R = 25\text{ V}$	I_R	10	nA
Capacitance Between Terminals at $V_R = 6\text{ V}$, $f = 1\text{ MHz}$	C_T	1.2	pF
Forward Operating Resistance at $I_F = 2\text{ mA}$, $f = 100\text{ MHz}$	r_f	0.9	Ω



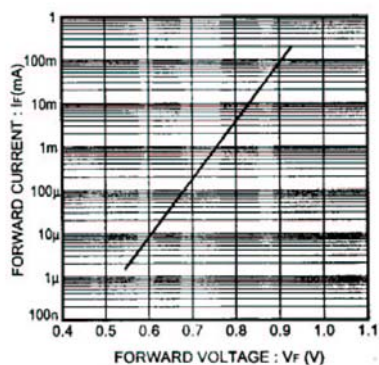


Fig. 1 Forward characteristics

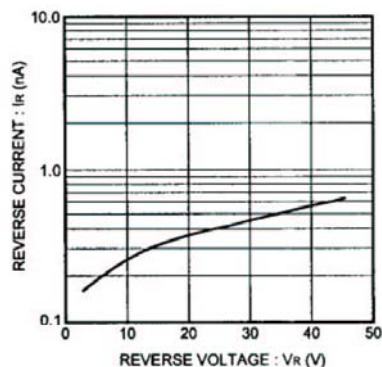


Fig. 2 Reverse characteristics

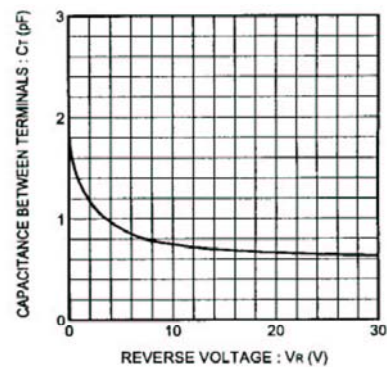


Fig. 3 Capacitance between terminals characteristics

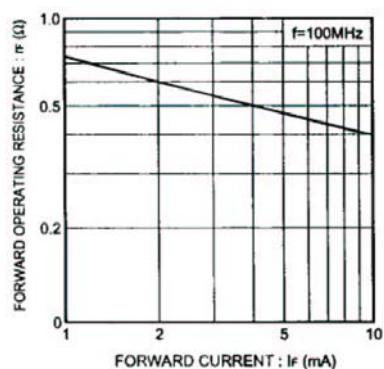
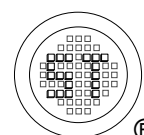


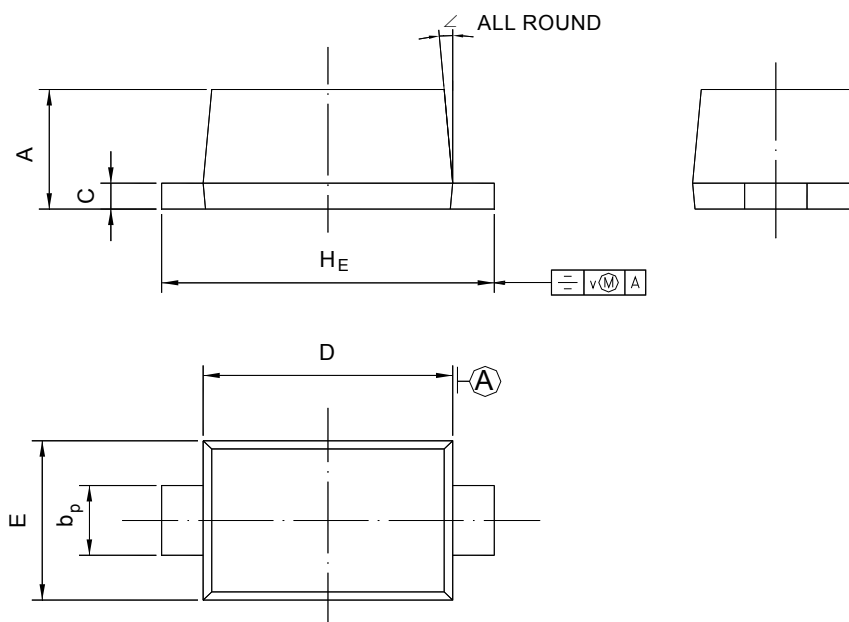
Fig. 4 Forward operating resistance characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°

